# UNIVERSITY OF SWAZILAND <br> MAIN EXAMINATION, FIRST SEMESTER <br> DECEMBER 2015 

FACULTY OF SCIENCE AND ENGINEERING

## DEPARTMENT OF ELECTRICAL AND ELECTRONIC

 ENGINEERINGTITLE OF PAPER: ANALOGUE DESIGN III COURSE CODE: EE421

TIME ALLOWED: THREE HOURS

INSTRUCTIONS:

1. There are five questions in this paper. Answer any FOUR questions. Each question carries $\mathbf{2 5}$ marks.
2. If you think not enough data has been given in any question you may assume any reasonable values.
3. Some useful formulas are given in the last page.

# THIS PAPER SHOULD NOT BE OPENED UNTIL PERMISSION HAS BEEN GIVEN BY THE INVIGILATOR 

THIS PAPER CONTAINS SEVEN (7) PAGES INCLUDING THIS PAGE

## QUESTION ONE ( 25 marks)

Consider the BJT amplifier shown in Figure-Q1.


Figure-01
(a) Under no input signal, calculate the collector voltage of $Q_{1}$ and $Q_{2}$, and also emitter and base voltage of $Q_{3}$. You may assume that the gains of the transistors are high. ( 6 marks)
(b) (i) Draw the common mode half circuits and derive an expression for the common mode gain for a single ended output, assuming that the impedance offered by the current source is $R_{o}$.
(ii) Calculate the common mode gain in (i) above.
(iii) What is the common mode gain if the output is taken differentially? Calculate this value if $R_{1}$ and $R_{2}$ are having a tolerance of $\pm 1 \%$.
(iv) Find an expression for the common mode input impedance and calculate its value.

Note:
(i) Output impedance of the current source $\approx r_{o}\left[1+\frac{R_{E}}{\frac{R_{E}+R_{B}}{\beta}+r_{e}}\right]$, in terms of usual notation.
(ii) Assume that the $\beta=100, V_{A}=80 \mathrm{~V}$ and $r_{\mu}=\infty$, unless otherwise stated.

## QUESTION TWO ( 25 marks)

In the NMOS amplifier shown in Figure-Q2, the devices $Q_{1}$ and $Q_{2}$ are matched.


Figure-Q2
(a) Calculate the value of the differential input voltage $V_{1}-V_{2}$, which will result $I_{D 2}=0.6 \mathrm{~mA}$.
(b) A differential input signal $v_{d}$ is applied to the amplifier. Draw the differential half circuits for mid band signals and calculate the differential gains $\frac{v_{01}}{v_{d}}, \frac{v_{o 2}}{v_{d}}$ and $\frac{v_{o}}{v_{d}}$ proving any formula you use.
(c) Calculate the maximum input common mode voltage range if the voltage drop across the current source is $V_{c s} \geq 3 V$.
(d) (i) Find the value of input offset voltage of the amplifier using the data given below.

$$
\begin{array}{ll}
\text { Tolerance of } R_{1} \text { and } R_{2} & = \pm 2 \% \\
\text { Tolerance of } \frac{w}{L} \text { ratio } & = \pm 4 \% \\
\text { Tolerance of } V_{t} & = \pm 0.2 \% \tag{4marks}
\end{array}
$$

(ii) Estimate the output dc voltage $V_{o}$ when the inputs $V_{1}=V_{2}=0$ if the tolerances given in d(i) are applicable.

## QUESTION THREE ( 25 marks)

(a) A cascode NMOS amplifier is shown in Figure-Q3, in which the transistors $Q_{1}$ and $Q_{2}$ are matched.


> Figure - Q3

Assume the following data of the devices given with usual notation.

$$
g_{m}=1.35 \frac{\mathrm{~mA}}{\mathrm{~V}} \quad \chi=0.2 \quad r_{o}=25 k \quad C_{g s}=18 f F \quad C_{g d}=4 f F \quad C_{d b}=5 f F
$$

(a) Show that the output impedance $R_{o}$ is given by, $R_{o}=r_{o 1}+r_{o 2}+r_{o 1} r_{o 2}\left(g_{m 2}+g_{m b 2}\right)$. (6 marks)
(b) Derive an expression for the mid-band gain $\frac{v_{o}}{v_{i}}$ and calculate its value.
(7 marks)
(c) Finding the Miller's components or otherwise, calculate the upper cutoff frequency $f_{H}$.
(9 marks)
(d) Calculate the unity gain frequency $f_{T}$ of the amplifier.

Note: You may use, $R_{i 2}=\frac{R_{L}+r_{o 2}}{1+r_{o 2} g_{m 2}^{l}}$

## OUESTION FOUR (25 marks)

(a) Consider the IC amplifier shown in Figure-Q4(a), with the following data.
$K_{1}=5 \frac{m A}{V^{2}}$
$K_{2}=3 \frac{m A}{v^{2}}$
$K_{3}=2 \frac{m A}{V^{2}}$
$\left|V_{t}\right|=1.5 V$
$\left|V_{A}\right|=70 \mathrm{~V}$
$I_{\text {ref }}=0.8 \mathrm{~mA}$
(i) Calculate the value of $R$ and the bias current of $Q_{3}$.
(4 marks)
(ii) Derive an expression for the voltage gain $\frac{v_{0}}{v_{i}}$ and calculate its value.
( 5 marks)
(iii) Estimate the maximum peak to peak value of the output signal at $v_{0}$, which can be obtained without any distortion.
(4 marks)


Figure - Q4(a)


Figure-Q4(b)
(b) In Figure-Q4(b), the devices $Q_{1}$ and $Q_{2}$ are enhancement and depletion type respectively. You may assume the data given below.

$$
\begin{array}{llrr}
W_{1}=80 \mu m & L_{1}=5 \mu m \\
V_{t D}=-2 V & \left.\mu C_{O X}=150 \frac{\mu A}{V^{2}} \quad W_{2}=5 \mu m \quad V_{A} \right\rvert\,=50 V \quad \chi=0.2 & V_{t E}=1 V
\end{array}
$$

(i) Calculate the drain current of $Q_{1}$ at no signal.
(ii) Draw the small signal equivalent circuit considering the body effect and the output resistance. Hence derive an expression for the voltage gain $\left(\frac{v_{o}}{v_{i}}\right)$ and calculate its value.

## QUESTION FIVE (25 marks)

(a) A circuit of a dc voltage regulator using a NPN Darlington pass transistor is shown in Figure-Q5(a).
(i) Calculate the output voltage.
(ii) Estimate the minimum value of $V_{\text {in }}$ that can be used with the regulator.
(iii) If the load current is $1 A$, calculate the power dissipation in the pass transistor for the case in (ii) above.

(b) The Figure-Q5(b) is a simplified circuit showing an IC regulator connected with a load resistance of $R_{L}$ associated with a load capacitance of $C_{b}$. The output capacitor of the regulator is shown as $C_{o}$, with its series equivalent resistance $R_{C}$. You may assume the following data.
$C_{o}=10 \mu F \quad R_{C}=2 \Omega \quad \mathrm{C}_{\mathrm{b}}=0.5 \mu \mathrm{~F} \quad \mathrm{R}_{\mathrm{L}}=33 \Omega$
$r_{d s(Q)}=65 \Omega \quad \mathrm{c}_{\mathrm{gs}(\mathrm{Q})}=200 \mathrm{pF}$
(i) Find the ratio of $\frac{R_{1}}{R_{2}}$, for an output voltage $V_{o}=3.3 \mathrm{~V}$.
(ii) If the resistances $R_{1}$ and $R_{2}$ are much larger than the $R_{L}, R_{C}$ and $r_{d s(Q)}$, investigate the stability of the circuit, clearly showing the steps followed. The unity gain crossover frequency of the loop gain is 14 kHz .

## 1. SOME USEFUL MOSFET EQUATIONS

$i_{D}=\mu_{n} C_{o x} \frac{W}{L}\left[\left(v_{G S}-v_{t}\right) v_{D S}-\frac{1}{2} v_{D S}^{2}\right]$ in triode region
$i_{D}=\frac{1}{2} \mu_{n} C_{o x} \frac{w}{L}\left(v_{G S}-v_{t}\right)^{2}$ in saturation region
$i_{D}=\frac{1}{2} \mu_{n} C_{o x} \frac{W}{L}\left(v_{G S}-v_{t}\right)^{2}\left(1+\lambda v_{D S}\right)$ in saturation region with Channel Modulation effect $V_{A}=\frac{1}{\lambda}$
2. Unless otherwise stated $V_{B E(O N)}=0.6 \mathrm{~V}$ and $V_{T}=0.025 \mathrm{~V}$.

